

### Internally Matched Power GaAs FETs (C-Band)

#### Features

- High power
  - $P_{1dB} = 36.0$  dBm at 7.1 GHz to 7.9 GHz
- High gain
  - $G_{1dB} = 6.5$  dB at 7.1 GHz to 7.9 GHz
- Broad band internally matched
- Hermetically sealed package

#### RF Performance Specifications ( $T_a = 25^\circ \text{C}$ )

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	$P_{1dB}$	$V_{DS} = 10V$ $f = 7.1 \sim 7.9 \text{ GHz}$	dBm	35.0	36.0	—
Power Gain at 1dB Compression Point	$G_{1dB}$		dB	5.5	6.5	—
Drain Current	$I_{DS}$		A	—	1.1	1.5
Power Added Efficiency	$\eta_{add}$		%	—	28	—
Channel-Temperature Rise	$\Delta T_{ch}$	$V_{DS} \times I_{DS} \times R_{th}(c-c)$	$^\circ\text{C}$	—	—	80

#### Electrical Characteristics ( $T_a = 25^\circ \text{C}$ )

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 1.5A$	mS	—	900	—
Pinch-off Voltage	$V_{GSoff}$	$V_{DS} = 3V$ $I_{DS} = 20mA$	V	-2	-3.5	-5
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 3V$ $V_{GS} = 0V$	A	—	2.9	3.8
Gate to Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -60 \mu A$	V	-5	—	—
Thermal Resistance	$R_{th}(c-c)$	Channel to case	$^\circ\text{C/W}$	—	4.0	6.0

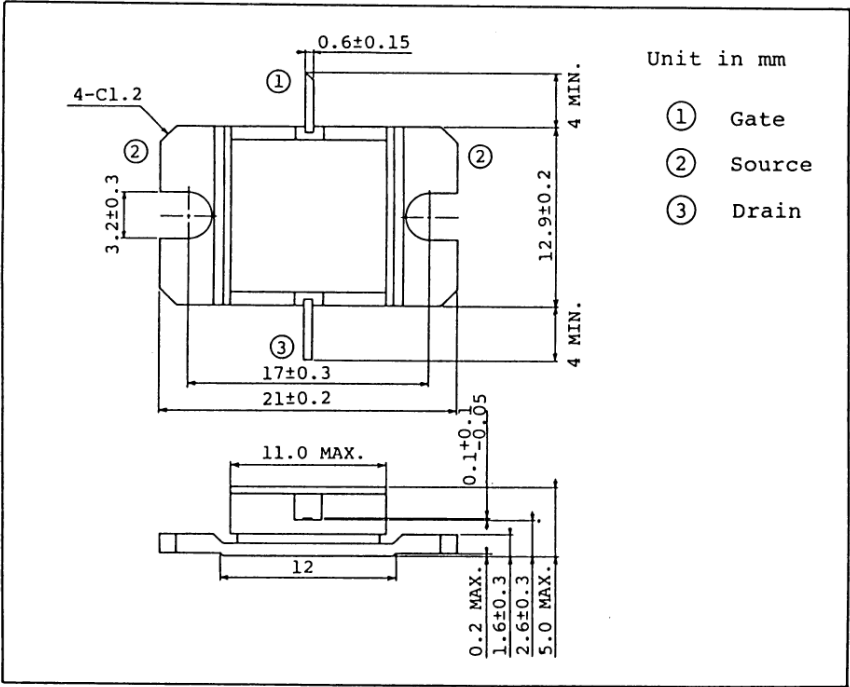
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Absolute Maximum Ratings (T<sub>a</sub> = 25° C)

Characteristic	Symbol	Unit	Rating
Drain Source Voltage	V <sub>DS</sub>	V	15
Gate Source Voltage	V <sub>GS</sub>	V	-5
Drain Current	I <sub>D</sub>	A	4
Total Power Dissipation (T <sub>c</sub> = 25°C)	P <sub>T</sub>	W	20
Channel Temperature	T <sub>ch</sub>	°C	175
Storage Temperature	T <sub>stg</sub>	°C	-65~175

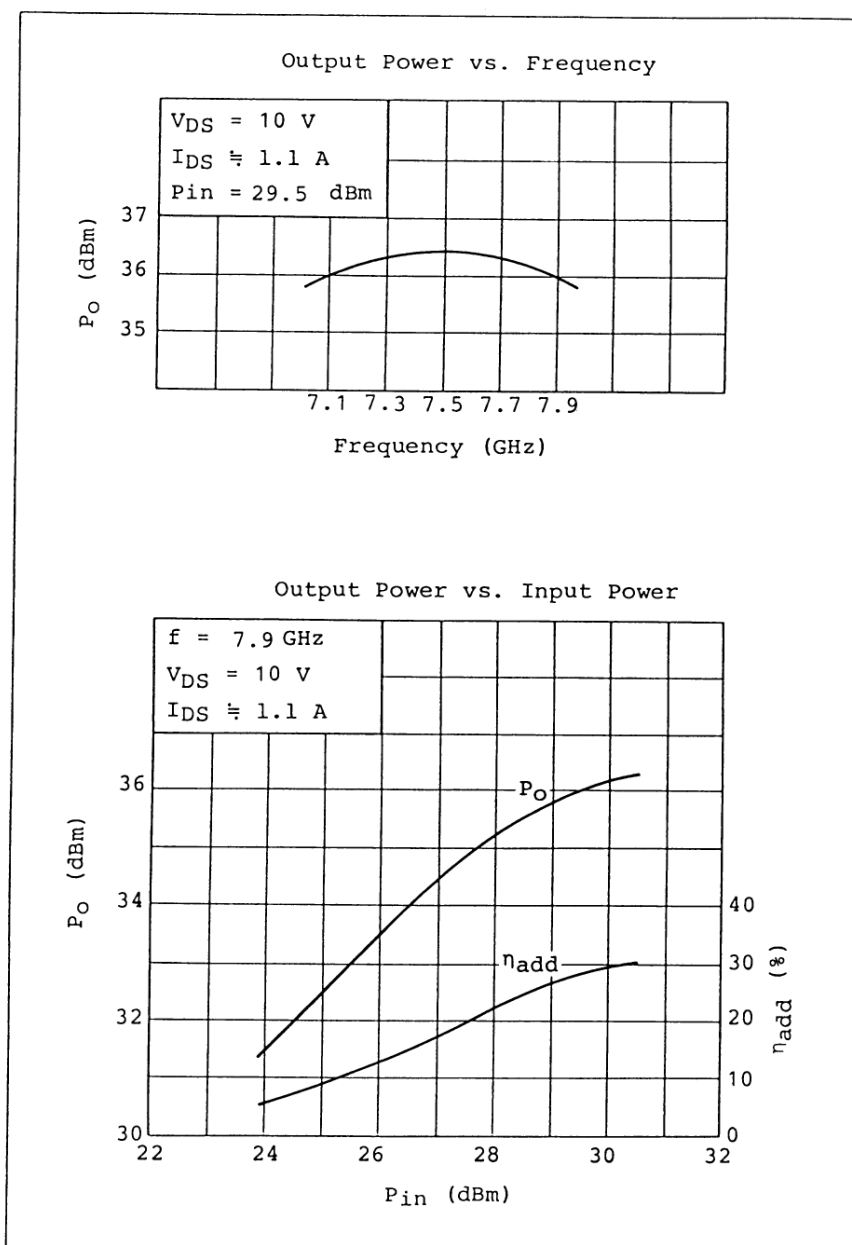
Package Outline (2-11D1B)



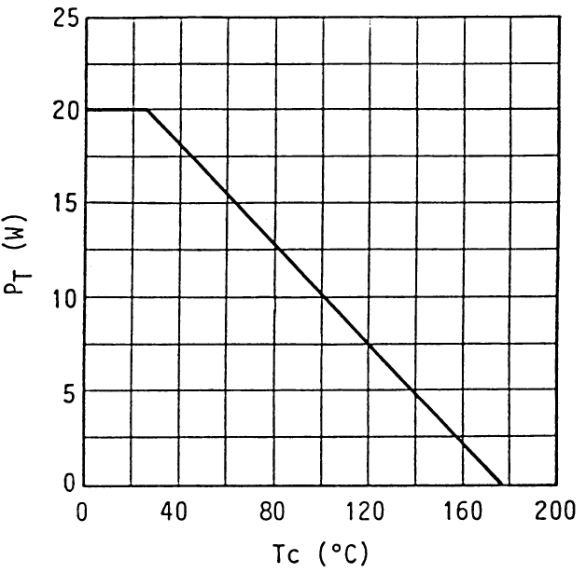
Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

## RF Performances



Power Dissipation vs. Case Temperature



**TIM7179-4 S-Parameters  
(MAGN. and ANGLES)**

$$V_{DS} = 10 \text{ V}, I_{DS} = 1.0 \text{ A}$$

$$f = 6.8\text{--}8.0 \text{ GHz}$$

